

NTNS41S006PZ

Small Signal MOSFET

–30 V, –130 mA, Single P–Channel,
0.62 x 0.62 x 0.4 mm XLLGA3 Package

Features

- Single P–Channel MOSFET
- Ultra Small and Thin Package (0.62 x 0.62 x 0.4 mm)
- Low $R_{DS(on)}$ Solution in 0.62 x 0.62 mm Package
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Small Signal Load Switch
- Analog Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Products

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Units	
Drain-to-Source Voltage		V_{DSS}	–30	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	–137	mA
			$T_A = 85^\circ\text{C}$	–99	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	–148		
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	121	mW
			$t \leq 5$ s	$T_A = 25^\circ\text{C}$	
Pulsed Drain Current		$t_p = 10 \mu\text{s}$	I_{DM}	–550	mA
Operating Junction and Storage Temperature		T_J, T_{STG}	–55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)		I_S	–137	mA	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	1035	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 5$ s (Note 1)	$R_{\theta JA}$	895	

1. Surface Mounted on FR4 Board using the minimum recommended pad size, (or 2 mm²), 1 oz Cu.
2. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.



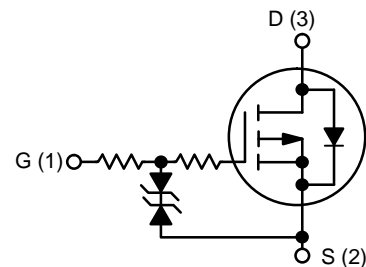
ON Semiconductor®

www.onsemi.com

MOSFET

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
–30 V	4.0 Ω @ –10 V	–130 mA
	7.0 Ω @ –4.5 V	

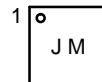
P–Channel MOSFET



MARKING DIAGRAM



XLLGA3
CASE 713AA



J = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NTNS41S006PZTCG	XLLGA3 (Pb–Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTNS41S006PZ

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -250 μA	-30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	I _D = -250 μA, ref to 25°C		32		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = -24 V			-1.0	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±12 V			±2.0	μA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250 μA	-1.0		-3.0	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			4.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = -10 V, I _D = -100 mA		2.1	4.0	Ω
		V _{GS} = -4.5 V, I _D = -50 mA		3.3	7.0	
Forward Transconductance	g _{FS}	V _{DS} = -5 V, I _D = -50 mA		0.14		S
Source-Drain Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = -50 mA		-0.8	-1.0	V

CHARGES & CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 10 kHz, V _{DS} = -15 V		9.1		pF
Output Capacitance	C _{OSS}			3.2		
Reverse Transfer Capacitance	C _{RSS}			1.9		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = -10 V, V _{DS} = -15 V, I _D = -100 mA		1.4		nC
Total Gate Charge	Q _{G(TOT)}	V _{GS} = -4.5 V, V _{DS} = -15 V, I _D = -100 mA		0.7		nC
Threshold Gate Charge	Q _{G(TH)}			0.3		
Gate-to-Source Charge	Q _{GS}			0.4		
Gate-to-Drain Charge	Q _{GD}			0.1		

SWITCHING CHARACTERISTICS, V_{GS} = -10 V (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = -10 V, V _{DD} = -15 V, I _D = -100 mA, R _G = 2 Ω		22.5		ns
Rise Time	t _r			33.1		
Turn-Off Delay Time	t _{d(OFF)}			178.9		
Fall Time	t _f			101.3		

SWITCHING CHARACTERISTICS, V_{GS} = -4.5 V (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = -4.5 V, V _{DD} = -15 V, I _D = -100 mA, R _G = 2 Ω		58.7		ns
Rise Time	t _r			137.3		
Turn-Off Delay Time	t _{d(OFF)}			78.6		
Fall Time	t _f			99.7		

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

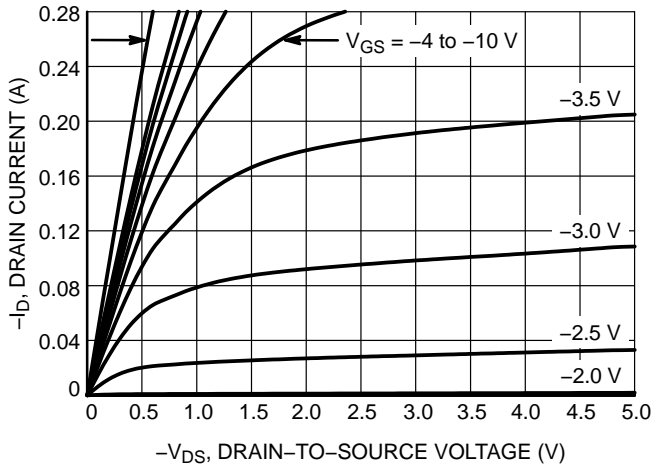


Figure 1. On-Region Characteristics

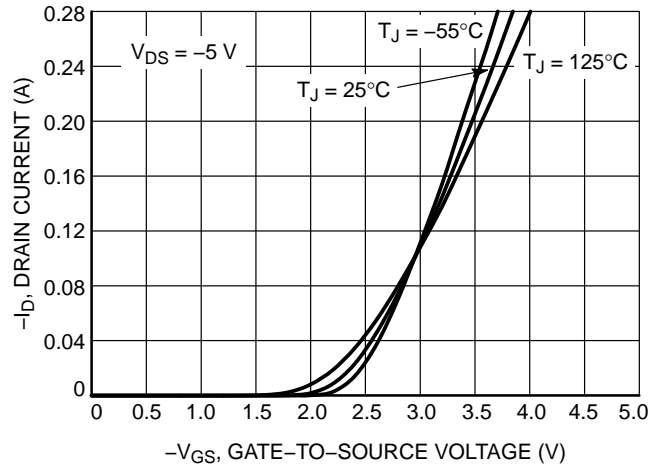


Figure 2. Transfer Characteristics

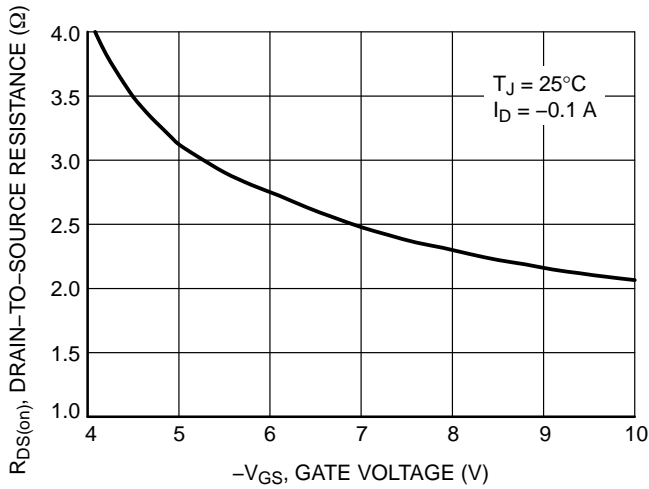


Figure 3. On-Resistance vs. Gate-to-Source Voltage

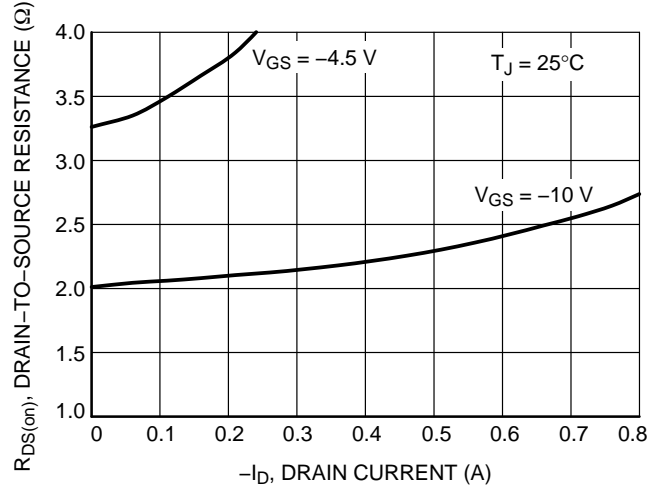


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

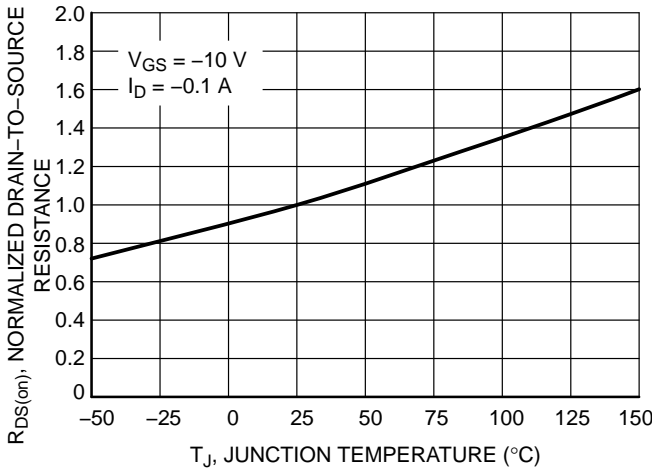


Figure 5. On-Resistance Variation with Temperature

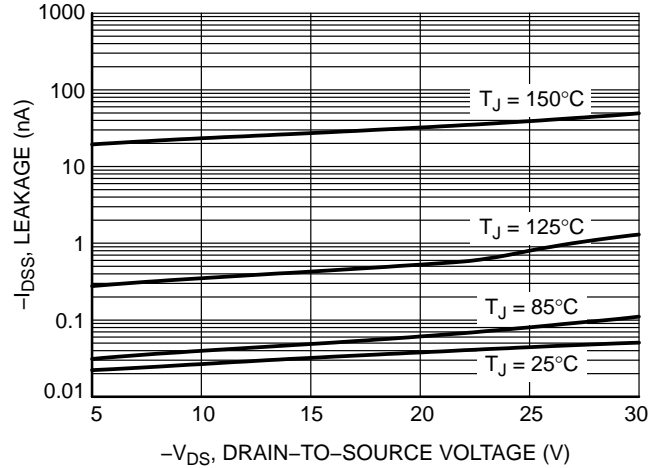


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

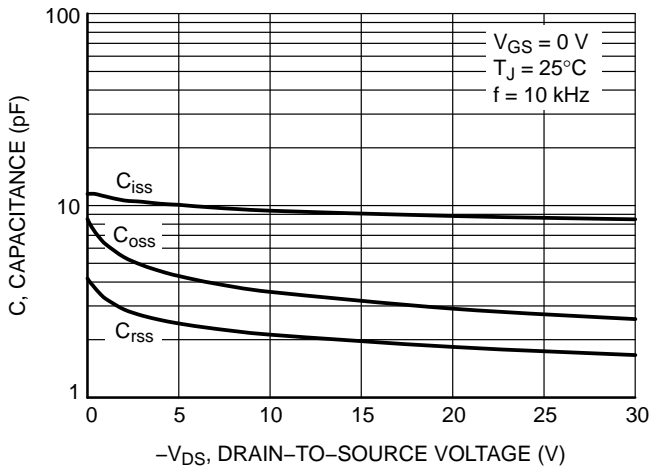


Figure 7. Capacitance Variation

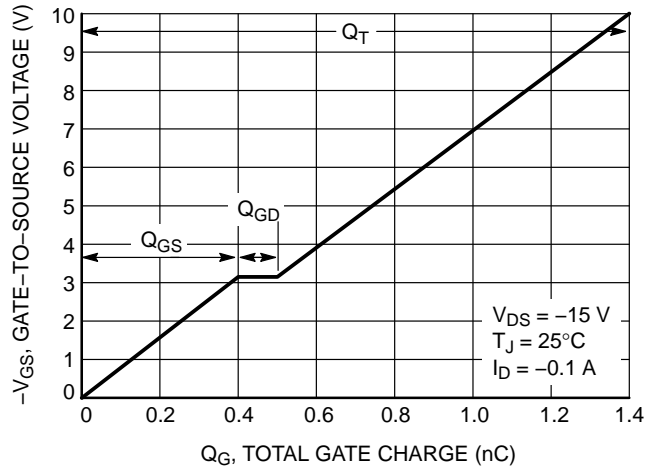


Figure 8. Gate-to-Source vs. Total Charge

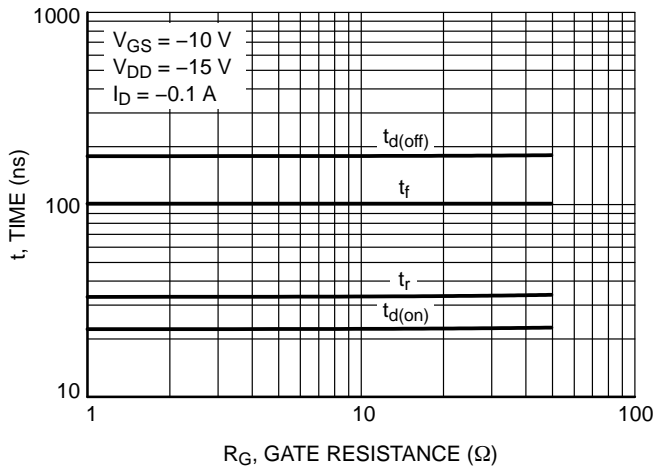


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

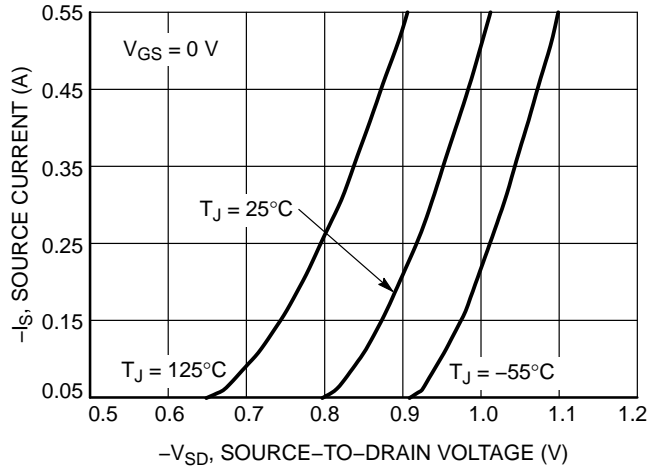


Figure 10. Diode Forward Voltage vs. Current

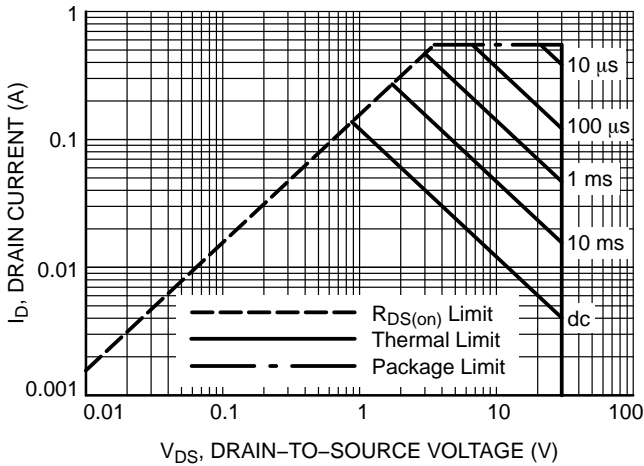


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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TYPICAL CHARACTERISTICS

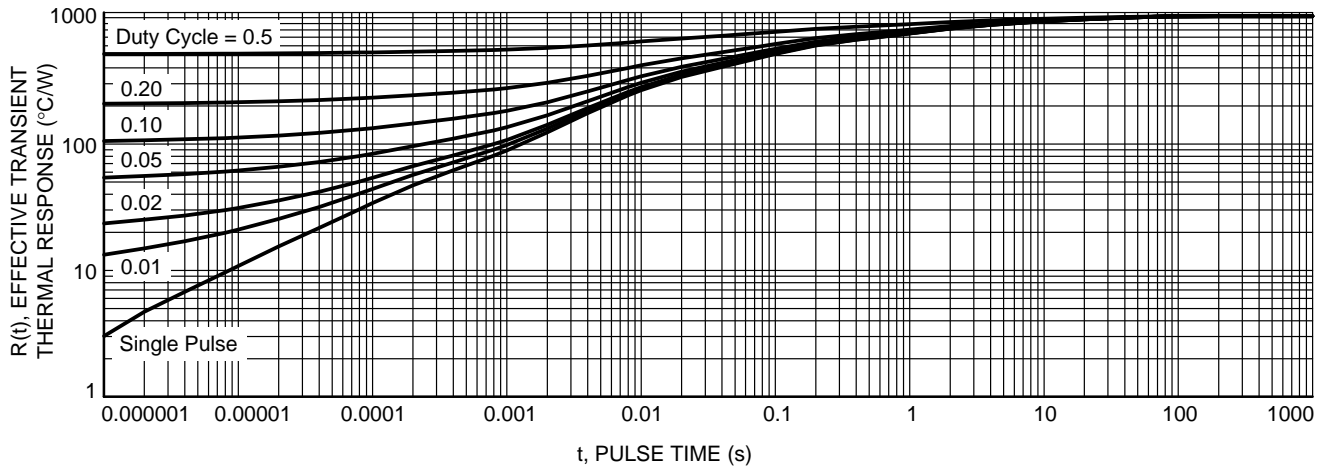
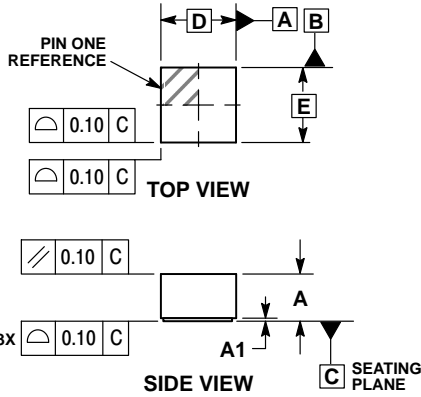


Figure 12. FET Thermal Response

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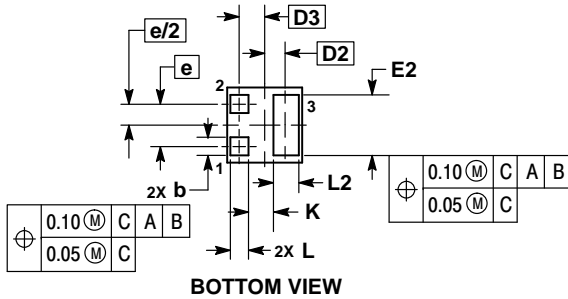
PACKAGE DIMENSIONS

XLLGA3, 0.62x0.62, 0.35P
CASE 713AA
ISSUE B

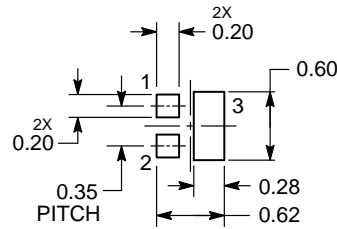


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.

MILLIMETERS		
DIM	MIN	MAX
A	0.340	0.440
A1	0.000	0.030
b	0.100	0.200
D	0.620 BSC	
D2	0.175 BSC	
D3	0.205 BSC	
E	0.620 BSC	
E2	0.400	0.600
e	0.350 BSC	
K	0.200 REF	
L	0.090	0.210
L2	0.110	0.310



MINIMUM RECOMMENDED SOLDER FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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